

The ZMS070N10I combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

device constructure
 $R_{DS(ON)}$ to minimize conduction loss
 fast switching

$T_C = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	70	A
	$I_{D@TC=75}$	57	A
	$I_{D@TC=100}$	47	A
Pulsed Drain Current	I_{DM}	280	A
Total Power Dissipation	$P_D@TC=25$	100	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	50	mJ



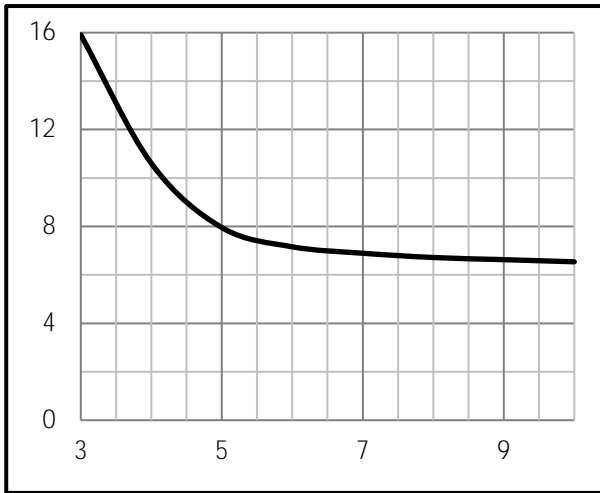


Fig.9 Switching Time Measurement Circuit

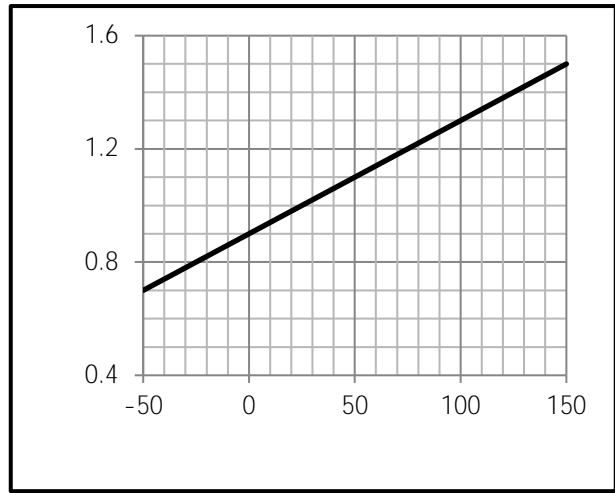


Fig.10 Gate Charge Waveform

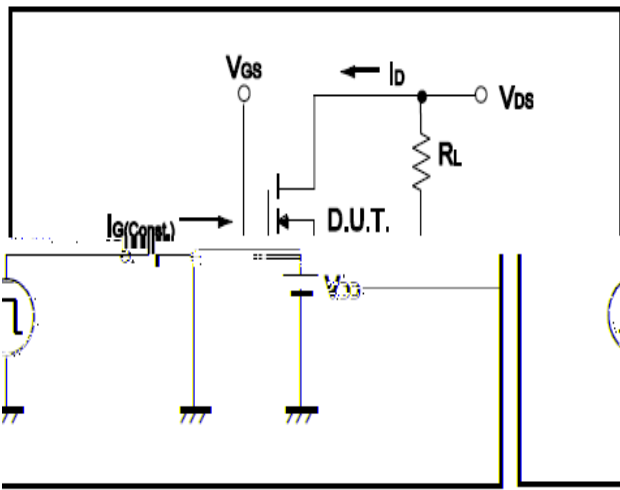


Fig.11 Switching Time Measurement Circuit

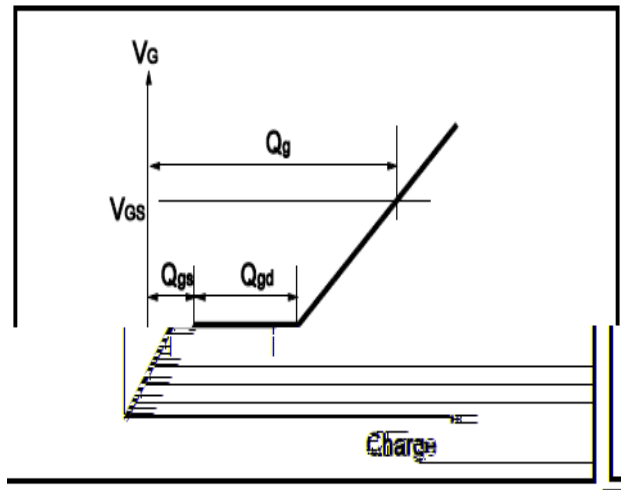
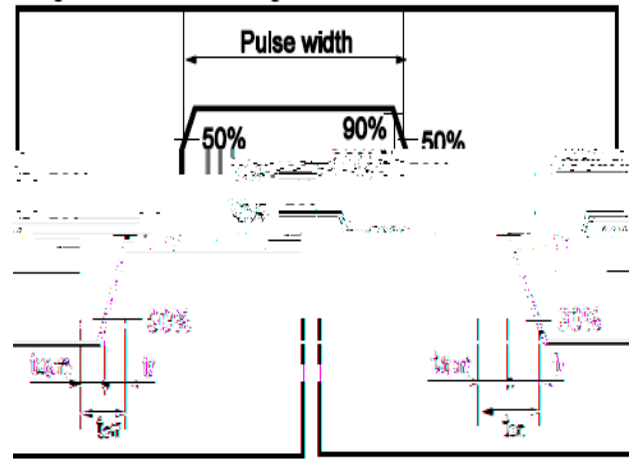
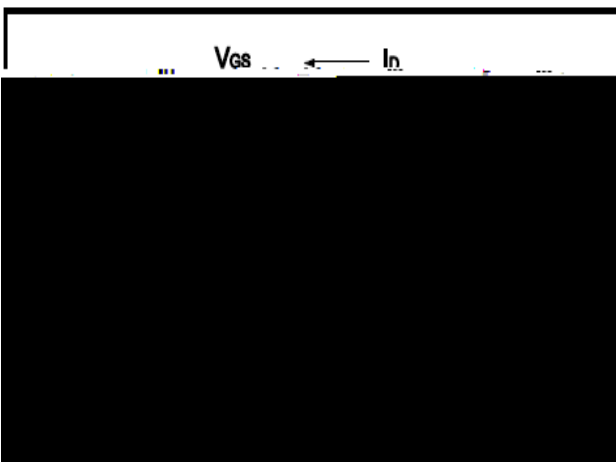


Fig.12 Gate Charge Waveform





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Unit mm

SYMBOL	mi n	max	SYMBOL	mi n	max
A	2.10	2.50	D	6.35	6.80
A1	0.95	1.30	D1	5.10	5.50
B	0.80	1.25	E	5.30	6.30
b	0.50	0.80	e	2.24	2.35
b1	0.70	0.90	E1	4.43	4.73